# A New Technique for Suppression of Spurious Responses in an Aluminum Nitride Based Thin Film Bulk Acoustic Resonator

窒化アルミニウムを用いた圧電薄膜共振子におけるスプリア ス抑制手法の提案

Motoaki Hara<sup>†</sup>, and Hiroki Kuwano (Grad. School of Eng., Tohoku Univ.) 原 基揚<sup>‡</sup>, 桑野 博喜 (東北大 工学研究科)

## 1. Introduction

A thin film bulk acoustic resonator (FBAR) is suitable for GHz band applications, and accepted for commercial duplexers [1]. The FBAR has a sandwich-like structure, which composed from top and bottom electrodes and a piezoelectric film.

Aluminum nitride (AlN) is adopted generally as a piezoelectric film for the FBAR, since it is relatively easy for AlN to be deposited with highly c-orientaion by a reactive sputtering. Furthermore, AlN doesn't contain a metal which plays a recombination center in a semiconductor. It open a possibility up for integration of active circuits and acoustic devices.

However, in the dispersion relation of the AlN plate, an  $S_1$  mode which is used in the FBAR mainly has a negative group velocity in the vicinity of cutoff frequency. Therefore the AlN based FBAR suffers from many spurious responses (*SRs*) beneath the resonance frequency. When such FBARs are applied to a ladder type filter, *SRs* from series resonators are allocated within the pass band, and deteriorate an insertion loss and a skirt steepness of the filter.

In this report, suppression technique of *SRs* was discussed using a 2-dimensional (2D) finite element method (FEM) and a dispersion diagram. Finally, new technique for *SRs* suppression was proposed.

## 2. Calculation model

**Figure 1** shows geometry of FEM models. At first, resonance characteristics against the electrode size (*W*) were calculated using the model as shown in Fig. 1 (a). Results were plotted in **Fig. 2**. In this report, *SRs* were evaluated using the sum of spurious intensity by  $3^{rd}$  order.

It was observed from Fig. 2 that resonance characteristics fluctuated for the W, and its cycle length was about 1  $\mu$ m. This is corresponding to the half wavelength of an  $A_0$  mode as shown in **Fig. 3**. It was interpreted from these results that the

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hara@nanosys.mech.tohoku.ac.jp



Fig.1 Simulation models for the FEM analysis



fluctuation was originated from the phase of the  $A_0$  mode on the electrode edge.

The shape of FBAR is designed to elliptical or non-orthogonal square practically in order to apodize the *SRs*. So the fluctuation is also equalized. Therefore characteristics were evaluated using average values for the W in this report.

## 3. Conventional technique

Conventionally, *SRs* can be eliminated by the double step edge of electrode as shown in Fig. 1 (b) [2]. In this structure, selecting the right width of  $w_2$ , the phase of the  $S_1$  mode on the electrode edge is adjusted to obtain the "piston mode", and *SRs* are strongly suppressed.

However this technique suffers from the



degradation of Q factors because the main mode is spent partially for the phase adjusting [3]. Futhermore, this structure needs multi step lithography to fabricate, and leads the high manufacturing cost.

**Figure 4** shows characteristics of the conventional model against the width of  $w_2$ , when  $t_1$ ,  $t_2$  and  $w_1$  were fixed to 0.1 µm, 0.025 µm and 2 µm, respectively. It was confirmed that *SRs* was strongly suppressed but *Q* factors were degraded.

#### 4. Proposed technique

From Fig.2, it was observed that the  $A_0$  mode influences the resonance characteristics. If the  $A_0$  mode can be used to induce the piston mode, *SRs* are cancelled without the degradation of Q factors.

**Figure 5** shows characteristics calculated using the model as shown in Fig. 1(c). This structure is used to obtain the high anti-resonance Qin conventional [3]. However, *SRs* can be reduced with the same structure by decreasing the  $w_3$  to lower than  $\lambda/2$  of the  $A_0$  mode.

**Figure 6** shows a comparison of each structure as shown in Fig. 1. It was comfirmed that *SRs* were reduced without shriveling the *Q*-circle in the proposed technique.

### 5. Conclusion

Suppression of supurious responses (*SRs*) in the AlN thin film bulk acoustic resonator (FBAR) was discussed using a 2-dimensional (2D) finite element method (FEM) and a dispersion diagram. In this report, it was confirmed that the  $A_0$  mode influences the resonance characteristics, and we proposed the technique in which the  $A_0$  mode was used to obtain the "piston mode".

In this technque, the Q didn't deteriorate against the conventional technique though suppression of *SRs* was weak. This is suitable for the ladder type filter in which an excellent steepness is demanded on the high band edge.





Fig. 6 Q-circles of FBARs

Moreover this technique can contribute to the cost reduction of the filter because high Q and small *SRs* were achieved indipendently under the same fabrication process.

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